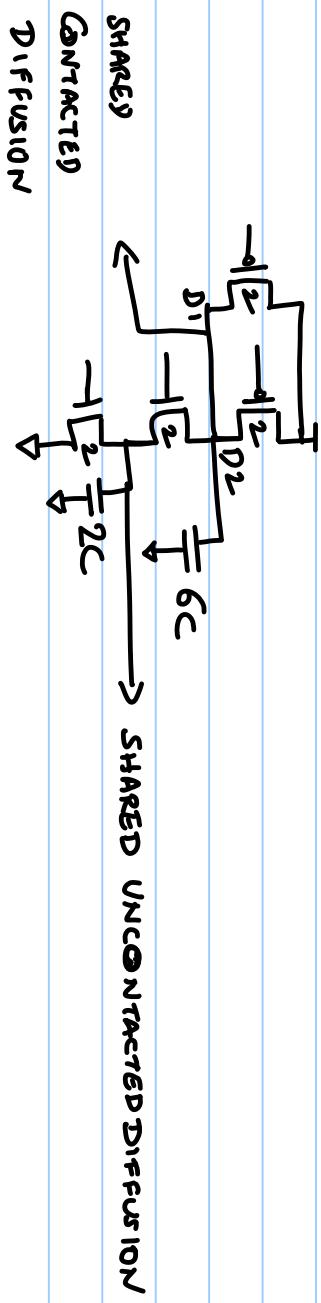


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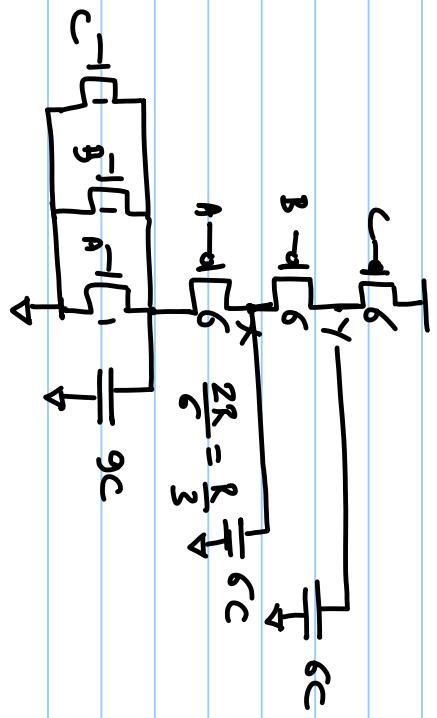
EE5311

Module-4 : Combinational Circuits

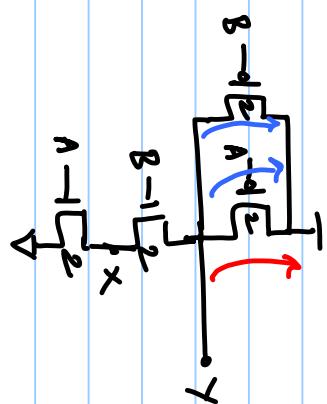


NOR₃

$$Y = \overline{A+B+C}$$



DELAY OF LOGIC GATES



$$\text{RISE DELAY} = \\ \text{FALL DELAY} =$$

PROPAGATION DELAY = WORST CASE DELAY
CONTAMINATION DELAY = BEST \sim -

RISE PROP DELAY :

$$\frac{1}{R} \quad Y = g_{RC}$$

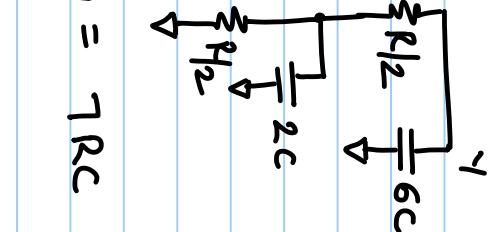
RISE CONT DELAY :

$$\frac{1}{R} \quad = 3RC$$

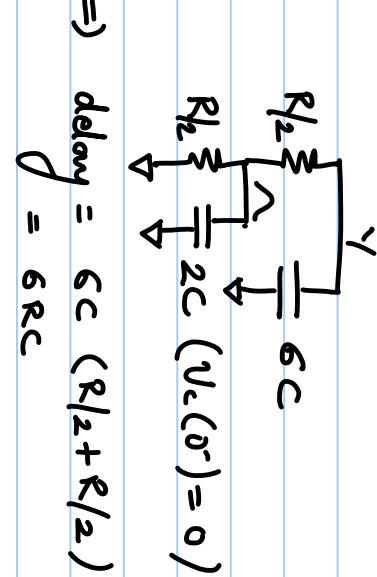
FALL DELAY (PROP) :

BOTH X & Y NEED TO DISCHARGE TO GND

INPUT A IS HIGH FOR
LONG. DISCHARGED NODE X
TO GND.



$$\text{delay} = \tau_{RC}$$



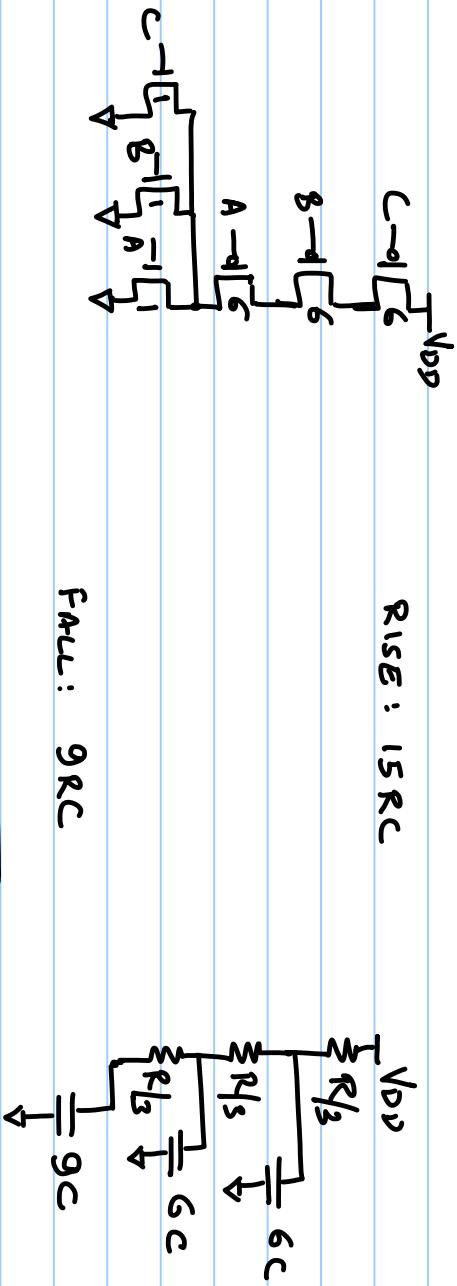
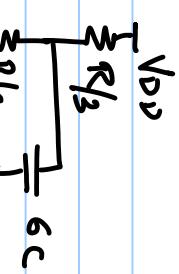
$$\Rightarrow \text{delay} = \tau_{RC}$$

NOR3 GATE: PROP DELAYS:

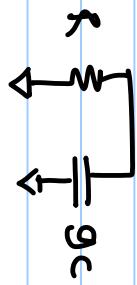


RISE: $15RC$

V_{DD}

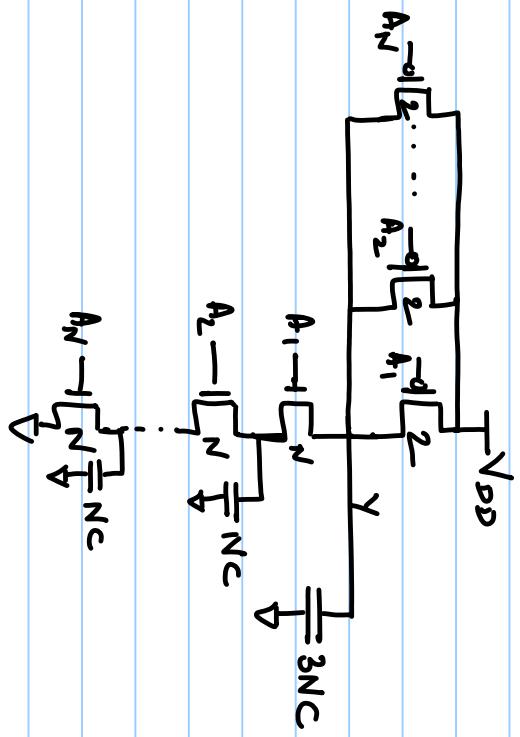


FALL: $9RC$



N-INPUT NMOS GATE (PROP DELAY)

$$\gamma = \frac{A_1 A_2 \dots A_N}{A_1 A_2 \dots A_N}$$

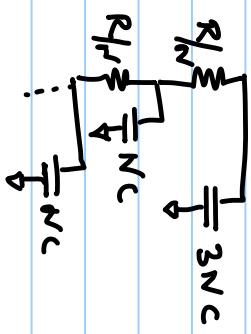


RISE :

$$\frac{R}{3NC}$$

$$\text{delay} = 3NRC$$

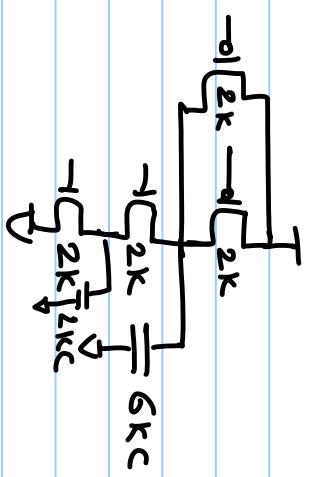
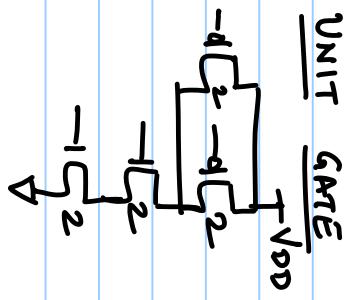
FALL :



$$\text{FALL DELAY} = 3NC(R) + NC \frac{(N-1)R}{N} + NC \frac{(N-2)R}{N} + \dots + NC \cdot \frac{R}{N}$$

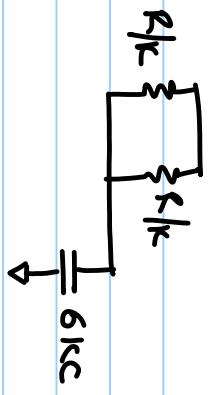
$$= \frac{N(N+5)}{2} RC$$

\Rightarrow DO NOT STACK MORE THAN 4 TRANSISTORS



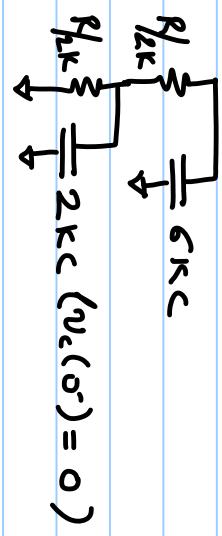
RISE

CONT



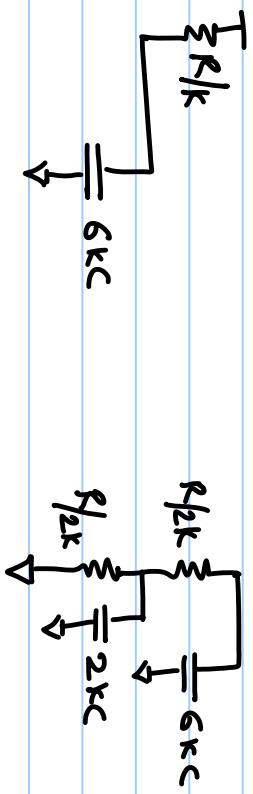
3RC

FALL



6RC

PROP



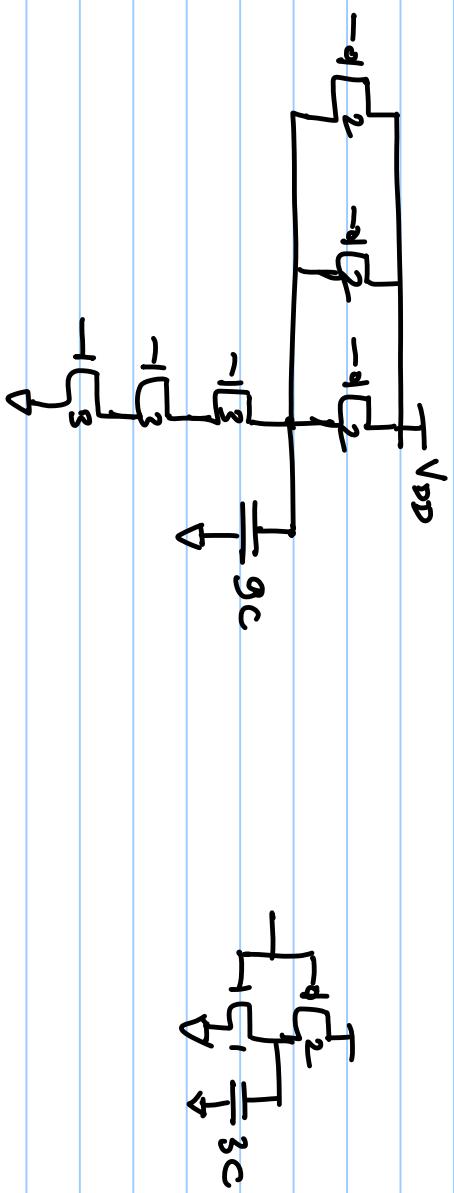
7RC

PARASITIC DELAY
IS INDEPENDENT

OF DRIVE STRENGTH

PARASITIC DELAY APPROXIMATION

COUNT TIME O/P DIFF CAP AND NORMALIZE TO CAP OF A
REF INV :



$$\frac{g_C}{3c} = 3.$$

$$\text{FOR } NAND_2 : \frac{g_C}{3c} = 2$$